



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638

Phone: (562) 404-7855 * Fax: (562) 404-1773

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**SDR998CT/3
thru
SDR9912CT/3**

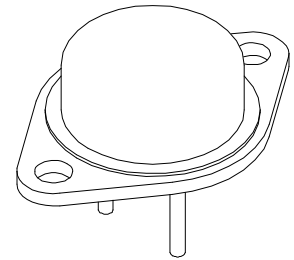
DESIGNER'S DATA SHEET

Features:

- Ultra Fast Recovery: 60 nsec typical
- High Surge Rating
- Low Reverse Leakage Current
- Low Forward Voltage Drop
- Low Junction Capacitance
- Hermetically Sealed Package
- Gold Eutectic Die Attach available
- Ultrasonic Aluminum Wire Bonds
- TX, TXV, Space Level Screening Available Consult Factory.

**100 AMP
800 -1200 Volts
80 nsec
ULTRA FAST COMMON CATHODE
CENTERTAP RECTIFIER**

TO-3



Maximum Ratings		Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking Voltage	SDR998CT/3	V_{RRM}	800	Volts
	SDR999CT/3		900	
	SDR9910CT/3	V_{RWM}	1000	
	SDR9911CT/3		1100	
	SDR9912CT/3	V_R	1200	
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, $T_A = 25^\circ\text{C}$)note 1		I_o	100	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave , $T_A = 25^\circ\text{C}$, per leg)		I_{FSM}	600	Amps
Operating & Storage Temperature		Top & Tstg	-65 to +200	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case, each individual diode Junction to Case, note 1		$R_{\theta JE}$	1.1 0.75	$^\circ\text{C/W}$

Note 1: Both legs in parallel

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RU0115B

DOC



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Electrical Characteristics		Symbol	Min	Max	Units
Instantaneous Forward Voltage Drop ($T_A = 25^\circ\text{C}$, 300 μsec pulse)	$I_F = 25\text{A dc}$ $I_F = 50\text{A dc}$	V_{F1}	—	1.85 2.1	Volts
Instantaneous Forward Voltage Drop ($T_A = -55^\circ\text{C}$, 300 μsec pulse) ($T_A = 100^\circ\text{C}$, 300 μsec pulse)	$I_F = 25\text{A dc}$ $I_F = 25\text{A dc}$	V_{F2}	—	1.75 1.9	Volts
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ\text{C}$, 300 μsec pulse minimum)		I_{R1}	—	100	μA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ\text{C}$, 300 μsec pulse minimum)		I_{R2}	—	10	mA
Junction Capacitance ($V_R = 10\text{ Vdc}$, $T_A = 25^\circ\text{C}$, $f = 1\text{MHz}$)		C_J	—	100	pF
Reverse Recovery Time ($I_F = 500\text{ mA}$, $I_R = 1\text{A}$, $I_{RR} = 0.25\text{A}$)	$T_A = 25^\circ\text{C}$	t_{rr}	—	80	nsec

